

Title (en)  
AMPLIFYING DEVICE COMPRISING A COMPENSATION CIRCUIT

Title (de)  
VERSTÄRKERVORRICHTUNG MIT EINER KOMPENSATIONSSCHALTUNG

Title (fr)  
DISPOSITIF D'AMPLIFICATION COMPRENANT UN CIRCUIT DE COMPENSATION

Publication  
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Application  
**EP 17752405 A 20170821**

Priority

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Abstract (en)  
[origin: WO2018036974A1] The present invention relates to an amplifying device (10) for amplifying an input signal, comprising: - a first amplification stage (12), - a second amplification stage (14), each amplification stage (12, 14) comprising: · a switching circuit (22), the switching circuit (22) being capable of generating, as output (22A, 22B), a switched signal having at least two states, and · an inductive element (24) capable of smoothing the switched signal in order to obtain a smoothed signal (I1, I3), the smoothed signal (I1, I3) having a useful component and a parasitic component. The amplifying device (10) further comprises a compensation circuit (16), for each amplification stage (12, 14), capable of generating a compensation signal (I2, I4) for compensating the parasitic component of the smoothed signal (I1, I3) generated in the inductive element (24) of said amplification stage (12, 14).

IPC 8 full level  
**H03F 3/185** (2006.01); **H03F 1/14** (2006.01); **H03F 3/30** (2006.01)

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